

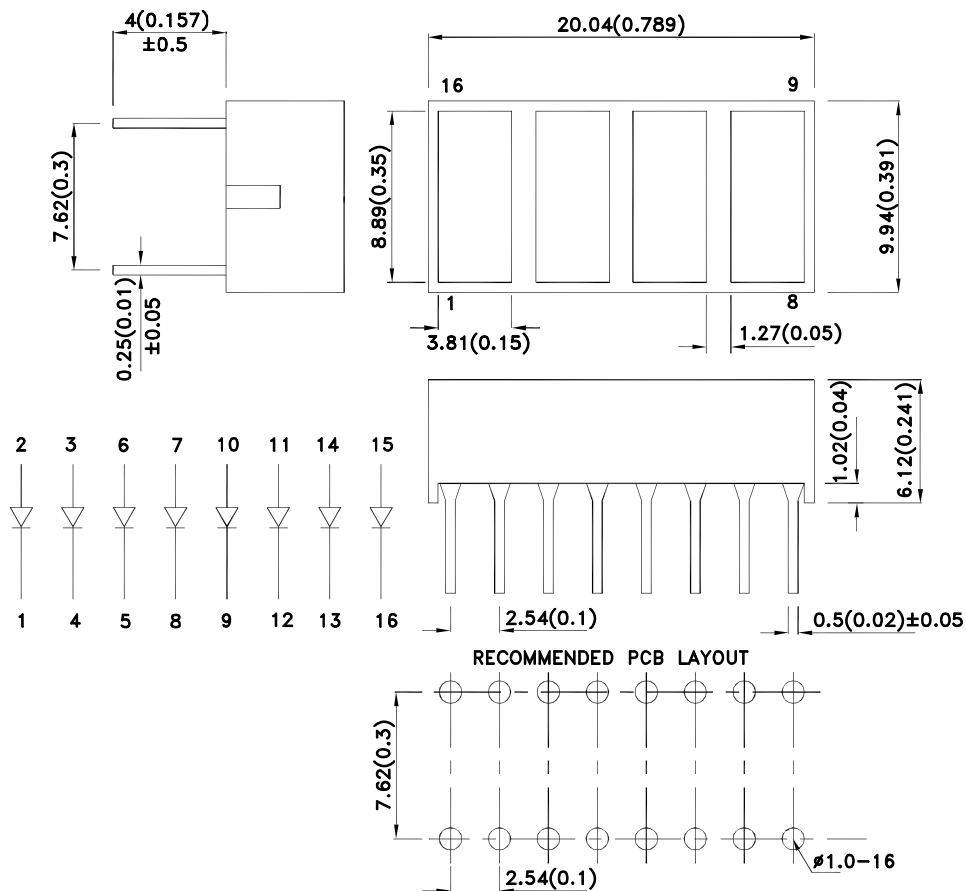
Features

- Uniform light emitting area.
- Low current operation.
- Easily mounted on P.C. boards.
- Flush mountable.
- Excellent on/off contrast.
- Can be used with panels and legend mounts.
- Categorized for luminous intensity.
- RoHS compliant.

Description

The Hyper Red source color devices are made with Al-GaN on GaAs substrate Light Emitting Diode.

Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches), Tolerance is ±0.25(0.01") unless otherwise noted.
2. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.



Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) [1] @ 20mA	
			Min.	Typ.
KB-E100SURKW	Hyper Red (AlGaInP)	WHITE DIFFUSED	70	210

Note:

1. Luminous intensity/ luminous Flux: +/-15%.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	Hyper Red	650		nm	I _F =20mA
λ_D [1]	Dominant Wavelength	Hyper Red	630		nm	I _F =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Hyper Red	28		nm	I _F =20mA
C	Capacitance	Hyper Red	35		pF	V _F =0V;f=1MHz
V _F [2]	Forward Voltage	Hyper Red	1.95	2.5	V	I _F =20mA
I _R	Reverse Current	Hyper Red		10	uA	V _R =5V

Notes:

- 1.Wavelength: +/-1nm.
2. Forward Voltage: +/-0.1V.

Absolute Maximum Ratings at TA=25°C

Parameter	Hyper Red	Units
Power dissipation	75	mW
DC Forward Current	30	mA
Peak Forward Current [1]	185	mA
Reverse Voltage	5	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

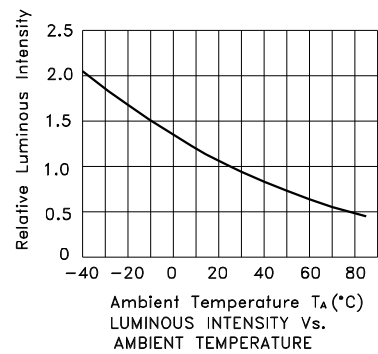
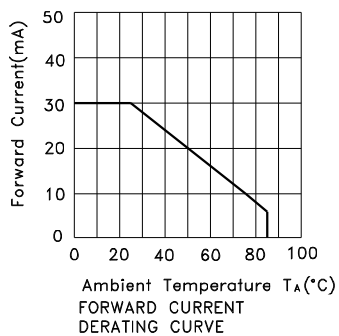
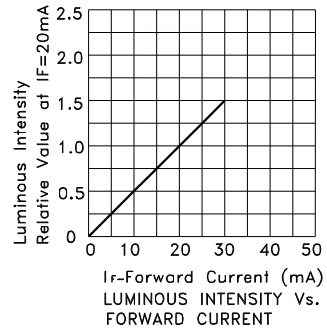
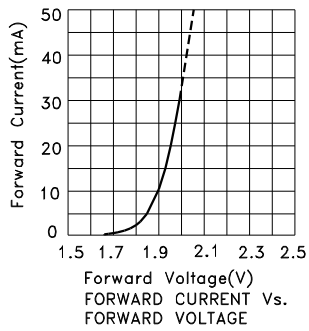
Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.



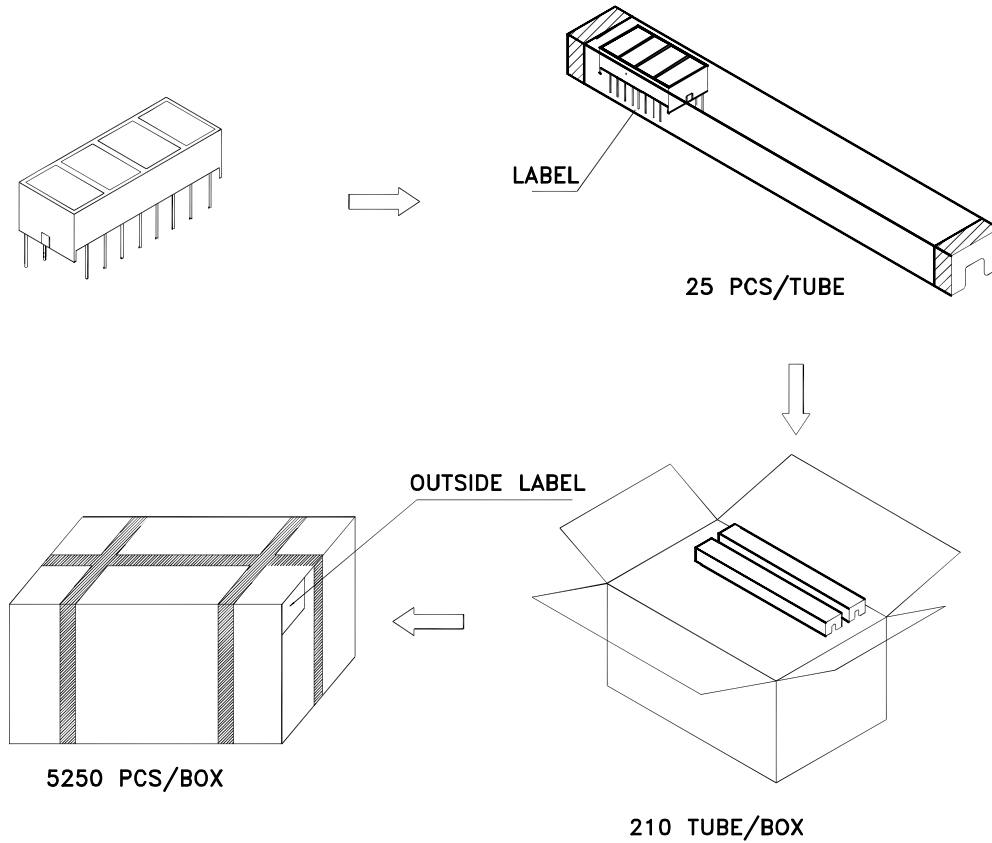
Hyper Red

KB-E100SURKW

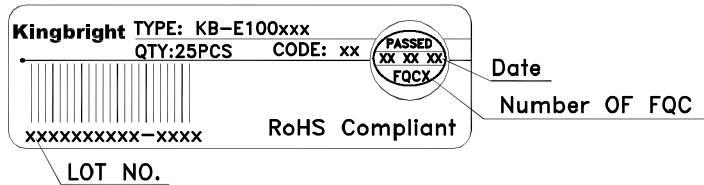


PACKING & LABEL SPECIFICATIONS

KB-E100SURKW



Inside Label Paste On The IC-tube



Outside Label Paste On The Box

